

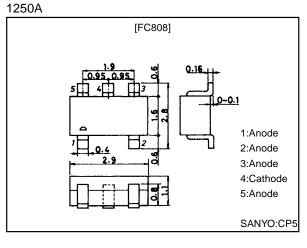
FC808 Silicon Epitaxial Plannar Type High-Speed Switching Composite Diode (Cathode Common)

Features

- Composite type with 4 diodes contained in the CP package currently in use, saving the mounting space greatly.
- · Fast switching speed.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	V _{RM}		85	V
Reverse Voltage	VR		80	V
Surge Current	IFSM	10ms*	2	A
Average Rectified Current	I _{O*}		100	mA
Peak Forward Current	IFM*		300	mA
Allowable Power Dissipation	P*		200	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

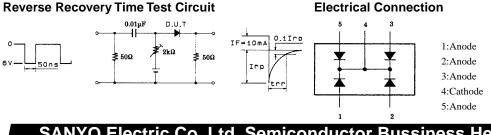
Note) *: Unit rating. The total rating is 150% of the unit rating.

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	٧ _F	I _F =10mA		0.72	1.0	V
		I _F =100mA		0.92	1.2	V
Reverse Current	I _R	V _R =50V			0.1	μΑ
		V _R =80V			0.5	μΑ
Interterminal Capacitance	С	V _R =0V, f=1MHz		4.0	7.0	pF
Reverse Recovery Time	trr	I _F =10mA, V _R =6V, R _L =5Ω, Irr=0.1Irp			5.0	ns

Note) The specifications shown above are for each individual diode.

· Marking:808



SANYO Electric Co., Ltd. Semiconductor Bussiness Headquarters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

22898HA (KT)/O3196GI/82093YH (KOTO) X-7219 No.4338-1/2

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